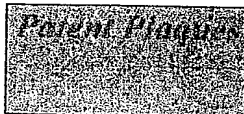


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JP6036966A2: THIN FILM CAPACITOR

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Country: **JP Japan**

Kind:

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Issued/Filed Dates: **Feb. 10, 1994 / May 26, 1992**

Application Number: **JP1992000133662**

IPC Class: **H01G 4/06; H01B 3/30; H01G 4/30; C08G 18/32; C08G 69/42; C08G 73/10;**

Abstract: **Purpose:** To obtain a thin film capacitor capable of further improving electric characteristics determined from the characteristics of a polymer layer formed as dielectric substance by a vapor deposition polymerization method.

Constitution: A thin film capacitor 1 is provided with a substrate 2 on which multilayered structure 5 constituted of film type inner electrodes 3a, 3b, 3c and film type dielectric substance 4a, 4b is formed. The dielectric substance 4a, 4b is composed of a polymer film of phloroalkylated aromatic polyimide containing N-methylacrididium-7,7,8,8-tetracyanoquino dimethane complex (which is called 'TCNQ complex' hereafter). The polymer film of phloroalkylated aromatic polyimide containing the TCNQ complex is formed by a vapor deposition polymerization method applying the following to evaporation source material; monomer of 2-2 bis (4-aminophenyl) hexaphloropropane, monomer of pyromellitic dihydride and crystal of TCNQ complex.

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Other Abstract Info: **DERABS C94-087082 DERC94-087082**

Foreign References: **(No patents reference this one)**

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(19)

(11) Publication number: 06036966

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PATENT ABSTRACTS OF JAPAN

(21) Application number: 04133662

(51) Intl. Cl.: H01G 4/06 H01B 3/30 H01G 4/30

(22) Application date: 26.05.92

(30) Priority:

(43) Date of application
publication: 10.02.94(84) Designated contracting
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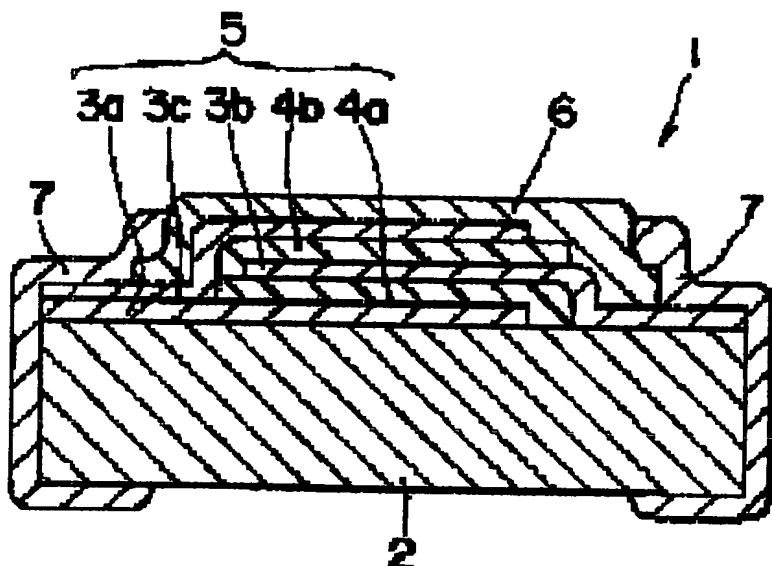
(74) Representative:

(54) THIN FILM
CAPACITOR

(57) Abstract:

PURPOSE: To obtain a thin film capacitor capable of further improving electric characteristics determined from the characteristics of a polymer layer formed as dielectric substance by a vapor deposition polymerization method.

CONSTITUTION: A thin film capacitor 1 is provided with a substrate 2 on which multilayered structure 5 constituted of film type inner electrodes 3a, 3b, 3c and film type dielectric substance 4a, 4b is formed. The dielectric substance 4a, 4b is composed of a polymer film of phloroalkylated aromatic polyimide containing N-methylacridimium-7,7,8,8-tetracyanoquinodimethane complex (which is called 'TCNQ complex' hereafter). The polymer film of phloroalkylated aromatic polyimide containing the TCNQ complex is formed by a vapor deposition polymerization method applying the following to evaporation source material; monomer of 2-2 bis (4-aminophenyl) hexaphloropropane,



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